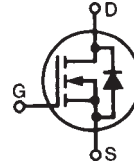


PolarHV™ HiPerFET Power MOSFET

IXFB 82N60P

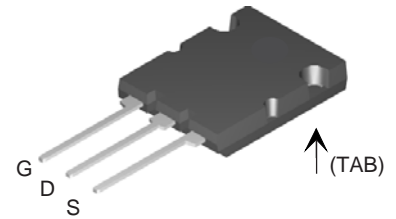
$V_{DSS} = 600 \text{ V}$
 $I_{D25} = 82 \text{ A}$
 $R_{DS(on)} \leq 75 \text{ m}\Omega$
 $t_{rr} \leq 200 \text{ ns}$

N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Diode



| Symbol | Test Conditions | Maximum Ratings | |
|---------------|-----------------------------------------------------------------------------------------------------------------------------------------|-------------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 600 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$ | 600 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 82 | A |
| I_{DRMS} | External lead current limit | 75 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 200 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 82 | A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 100 | mJ |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 5 | J |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$ | 20 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 1250 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.062 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| T_{SOLD} | Plastic body for 10 s | 260 | $^\circ\text{C}$ |
| F_C | Mounting force | 30..120/7.5...2.7 | N/lb |
| Weight | | 10 | g |

PLUS264™ (IXFB)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Plus 264™ package for clip or spring
- Space savings
- High power density

| Symbol | Test Conditions | Characteristic Values | | |
|--------------|---------------------------------------------------------------------------|-----------------------|------|----------------------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0 \text{ V}$, $I_D = 3 \text{ mA}$ | 600 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$ | 3.0 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 200 \text{ nA}$ |
| I_{DSS} | $V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$ | | | 25 μA 2000 μA |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$, Note 1 | | | 75 $\text{m}\Omega$ |

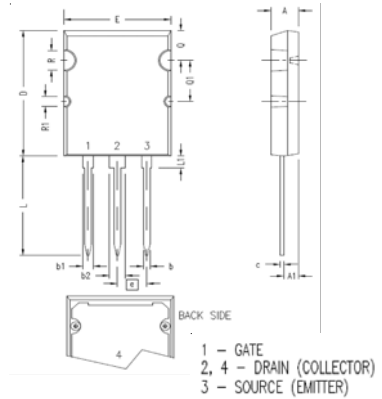
| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|-------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$, Note 1 | 50 | 80 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 23 | nF |
| C_{oss} | | | 1490 | pF |
| C_{rss} | | | 200 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$ (External) | | 28 | ns |
| t_r | | | 23 | ns |
| $t_{d(off)}$ | | | 79 | ns |
| t_f | | | 24 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ | | 240 | nC |
| Q_{gs} | | | 96 | nC |
| Q_{gd} | | | 67 | nC |
| R_{thJC} | | | 0.10 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.13 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|--------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 82 A |
| I_{SM} | Repetitive | | | 200 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ | | | 200 ns |
| Q_{RM} | | | 0.6 | μC |
| I_{RM} | | | 6.0 | A |

Notes:

1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

PLUS264™ (IXFB) Outline


| SYM | INCHES | | MILLIMETERS | |
|------------------|----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .185 | .209 | 4.70 | 5.31 |
| A1 | .102 | .118 | 2.59 | 3.00 |
| b | .037 | .055 | 0.94 | 1.40 |
| b1 | .087 | .102 | 2.21 | 2.59 |
| b2 | .110 | .126 | 2.79 | 3.20 |
| c | .017 | .029 | 0.43 | 0.74 |
| D | 1.007 | 1.047 | 25.58 | 26.59 |
| E | .760 | .799 | 19.30 | 20.29 |
| e | .215 BSC | | 5.46 BSC | |
| L | .779 | .842 | 19.79 | 21.39 |
| L1 | .087 | .102 | 2.21 | 2.59 |
| Q | .240 | .256 | 6.10 | 6.50 |
| Q1 | .330 | .346 | 8.38 | 8.79 |
| $\varnothing R$ | .155 | .187 | 3.94 | 4.75 |
| $\varnothing R1$ | .085 | .093 | 2.16 | 2.36 |

Fig. 1. Output Characteristics @ 25°C

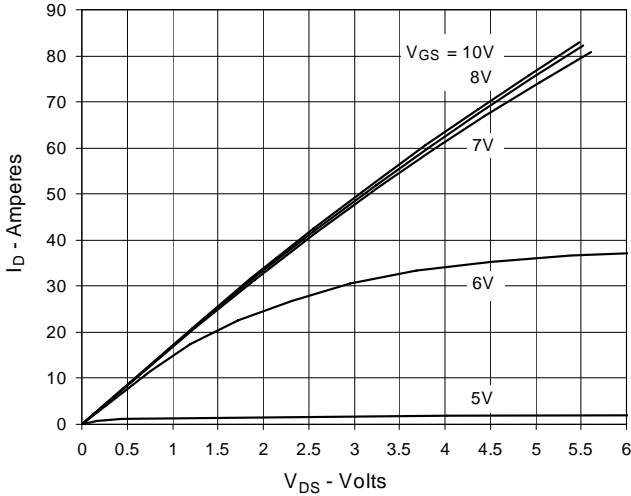


Fig. 2. Extended Output Characteristics @ 25°C

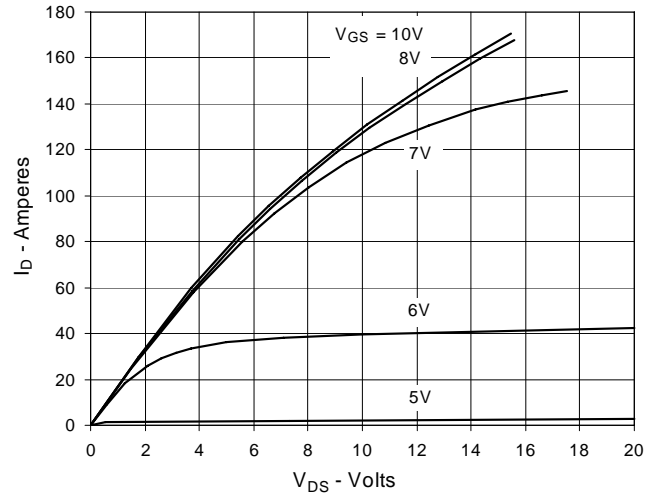


Fig. 3. Output Characteristics @ 125°C

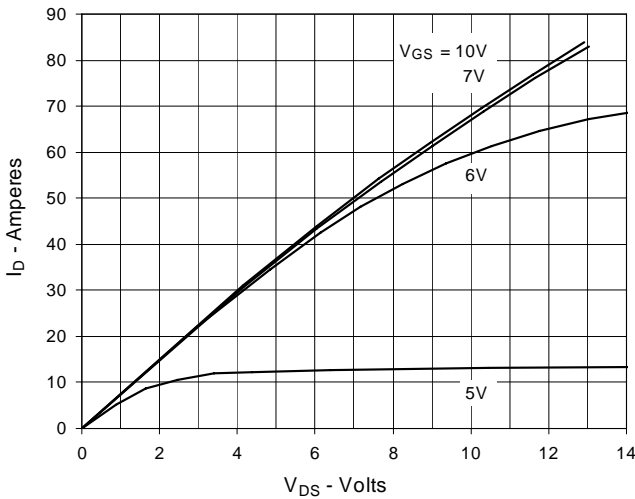


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 41A$ Value vs. Junction Temperature

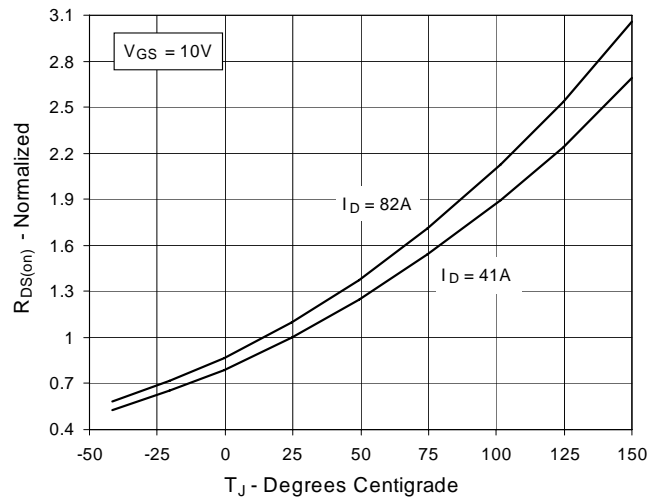


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 41A$ Value vs. Drain Current

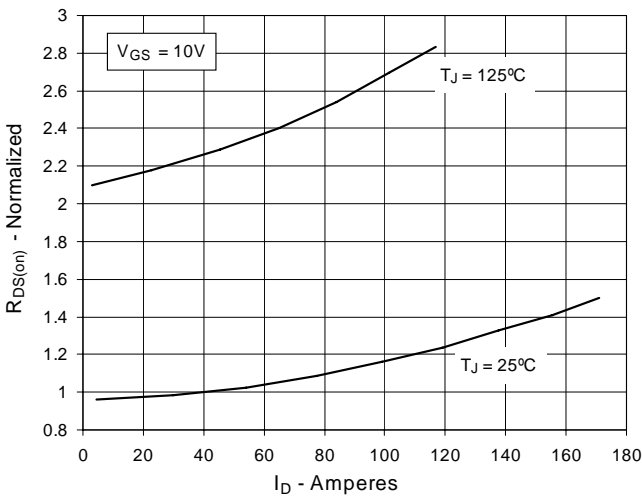


Fig. 6. Maximum Drain Current vs. Case Temperature

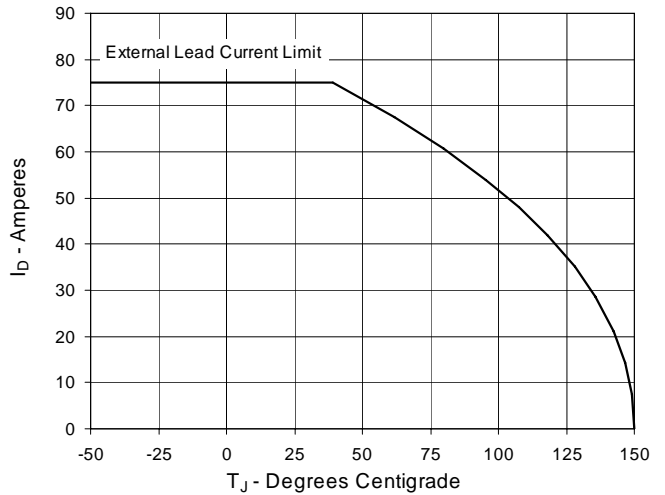


Fig. 7. Input Admittance

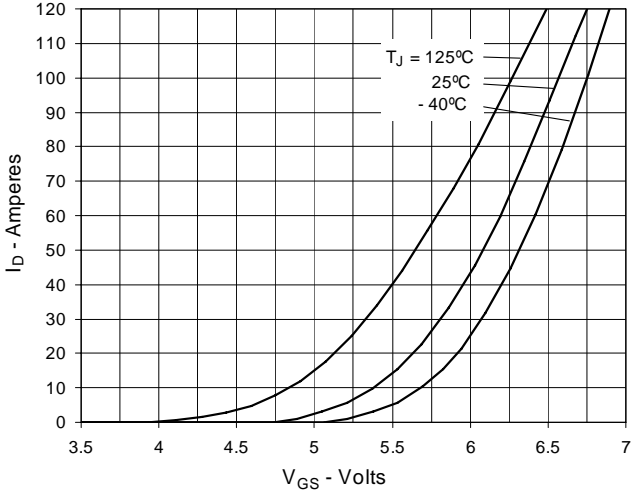


Fig. 8. Transconductance

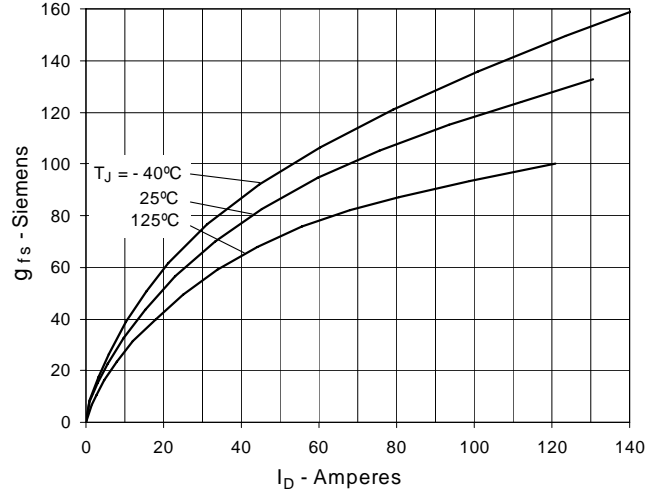


Fig. 9. Forward Voltage Drop of Intrinsic Diode

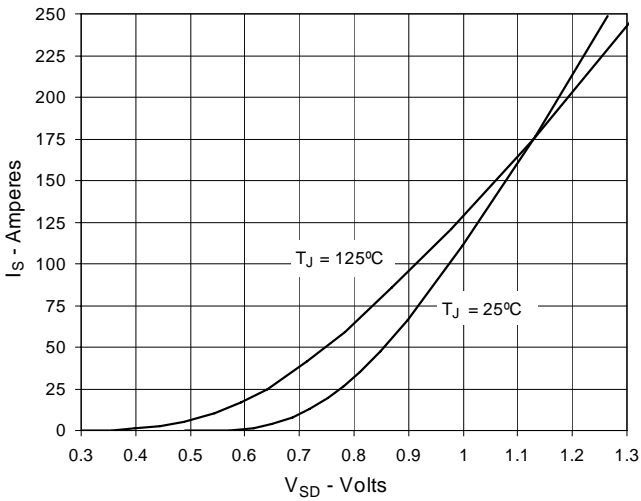


Fig. 10. Gate Charge

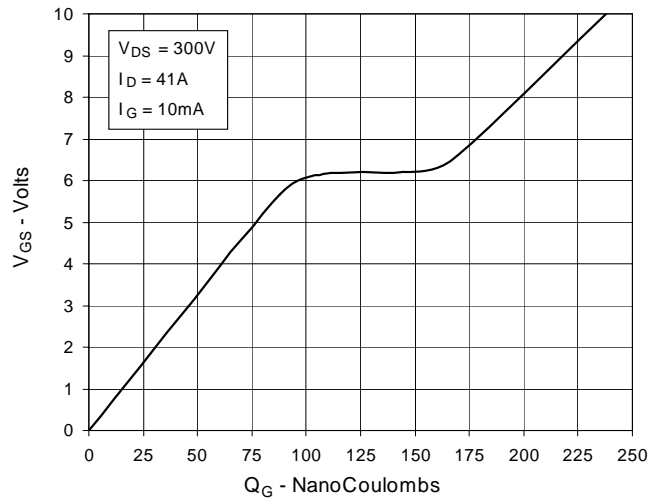


Fig. 11. Capacitance

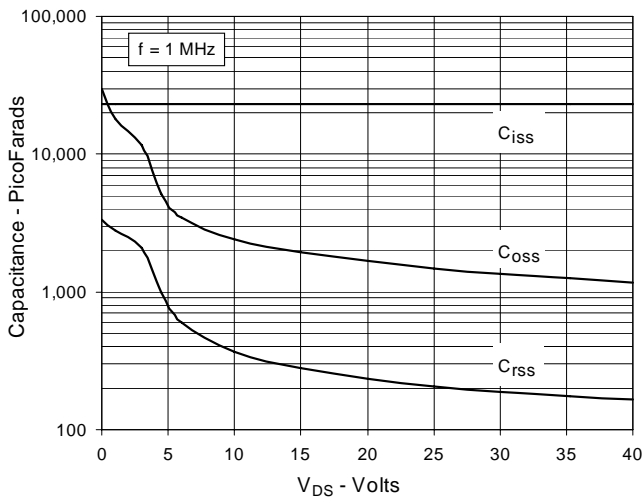


Fig. 12. Forward-Bias Safe Operating Area

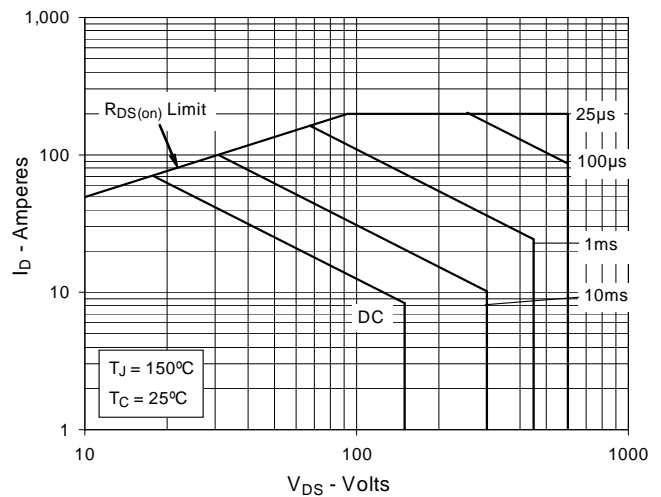
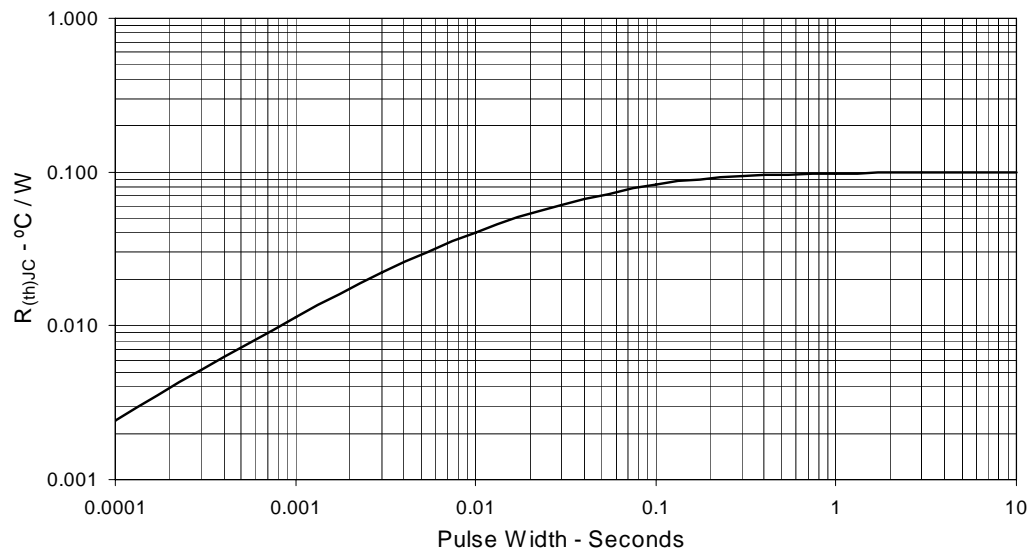


Fig. 13. Maximum Transient Thermal Resistance



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